

# ULC0511DN

### Features

- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±15kV
    - Contact discharge: ±10kV
- RoHS Compliant

## Dimensions SOD-882







## Applications

- USB 2.0 power and data line
- Set-top box and digital TV
- Digital video interface (DVI)
- Notebook Computers
- SIM Ports
- 10/100 Ethernet

## **Mechanical Characteristics**

- Package: SOD-882
- Lead Finish: Lead Free
- UL Flammability Classification Rating 94V-0
- Quantity Per Reel:1000pcs

### **Absolute Maximum Ratings**(Tamb=25°C unless otherwise specified)

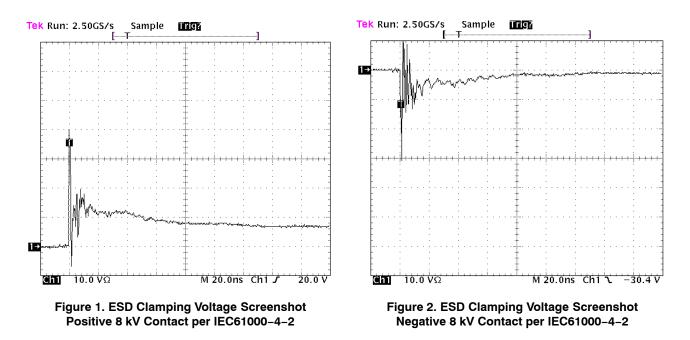
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ррр		W
ESD per IEC 61000-4-2 (Air)	- Vesd	±15	Kv
ESD per IEC 61000-4-2 (Contact)	VESD	±10	ι τν
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Тѕтј	-55 to +150	°C



### Electrical Characteristics(TA=25°C unless otherwise specified)

Part Number	Device Marking	V <sub>RWM</sub> (V)	Vbr (V)	I⊤ (mA)	Vc @1A	(Max)	c (@A)	I <sub>R</sub> μΑ (Max)	C (Pf) (Typ.)
ULC0511DN	D	5	5.4	1	9.8			1	0.5

## **Characteristic Curves**





#### IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

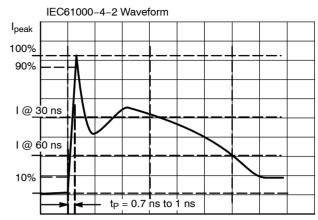


Figure 3. IEC61000-4-2 Spec

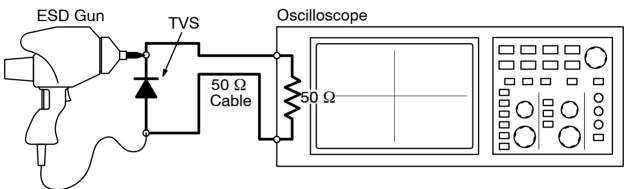


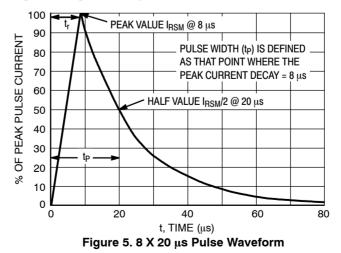
Figure 4. Diagram of ESD Test Setup

#### The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

#### **ESD Voltage Clamping**

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

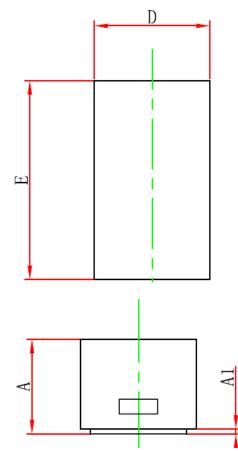
systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

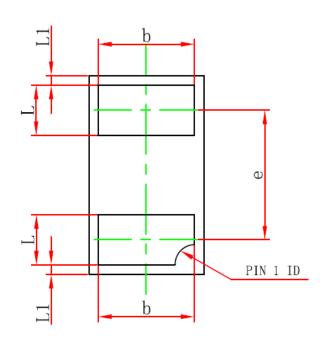






#### SOD882 Package Outline Drawing





Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	0.400	0.500	0.016	0.020	
A1	0.000	0.050	0.000	0.002	
D	0.550	0.650	0.022	0.026	
E	0.950	1.050	0.037	0.041	
b	0.400	0.600	0.016	0.024	
е	0.650TYP.		0.026TYP.		
L	0.150	0.350	0.006	0.014	
L1	0.050REF.		0.002REF.		

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